

Transient Voltage Suppressors

ESD Protection Diodes with Ultra-Low Capacitance

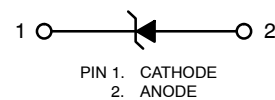
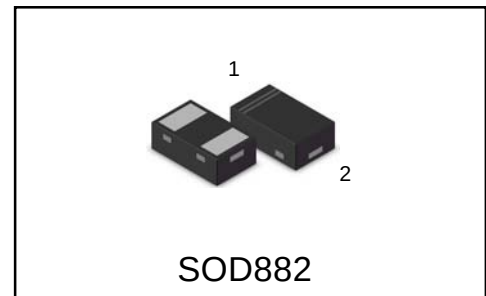
The ESD9 is designed to protect voltage sensitive components that require ultra-low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed and antenna line applications.

Specification Features:

- Ultra Low Capacitance 0.5 pF
- Low Clamping Voltage
- Small Body Outline Dimensions:
0.039" x 0.024" (1.00 mm x 0.60 mm)
- Low Body Height: 0.020" (0.5 mm)
- Stand-off Voltage: 3.3 V
- Low Leakage
- Response Time is Typically < 1.0 ns
- IEC61000-4-2 Level 4 ESD Protection
- This is a Pb-Free Device
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

QUALIFIED MAX REFLOW TEMPERATURE: 260°C

Device Meets MSL 1 Requirements



Ordering information

Device	Marking	Shipping
PESD9X3V3U	P	10000/Tape&Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Contact Air		±10 ±15	kV
Total Power Dissipation on FR-5 Board (Note 1) @ T _A = 25°C	P _D	150	mW
Storage Temperature Range	T _{stg}	-55 to +150	°C
Junction Temperature Range	T _J	-55 to +125	°C
Lead Solder Temperature – Maximum (10 Second Duration)	T _L	260	°C

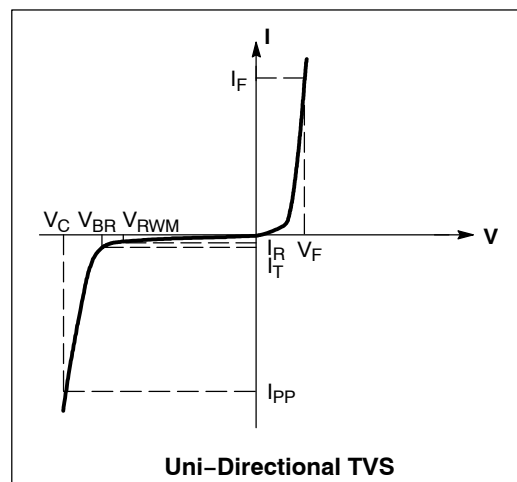
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0 x 0.75 x 0.62 in.

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_F	Forward Current
V_F	Forward Voltage @ I_F
P_{pk}	Peak Power Dissipation
C	Capacitance @ $V_R = 0$ and $f = 1.0$ MHz



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 1.0$ V Max. @ $I_F = 10$ mA)

Device	Device Marking	V_{RWM} (V)	I_R (μA) @ V_{RWM}	V_{BR} (V) @ I_T (Note 2)	I_T	C (pF)		V_C (V) @ $I_{PP} = 1$ A (Note 3)	V_C
		Max	Max	Min	mA	Typ	Max	Max	Per IEC61000-4-2 (Note 4)
PESD9X3V3U	P	3.3	1.0	4.8	1.0	0.5	0.9	12	Figures 1 and 2 See Below

- V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C .
- Surge current waveform per Figure 5.
- For test procedure see Figures 3 and 4.

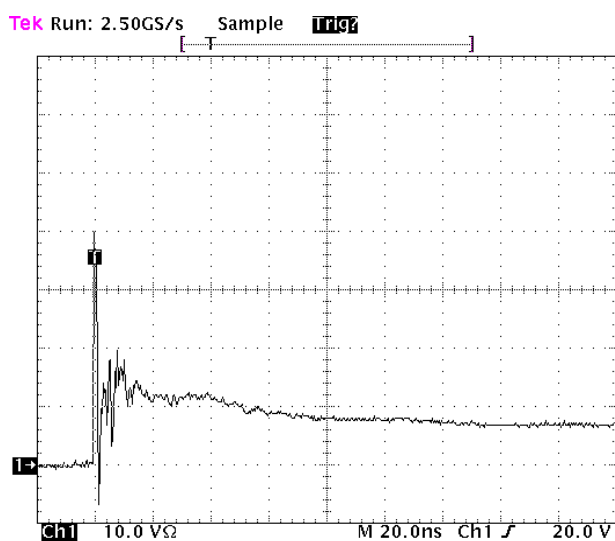


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2

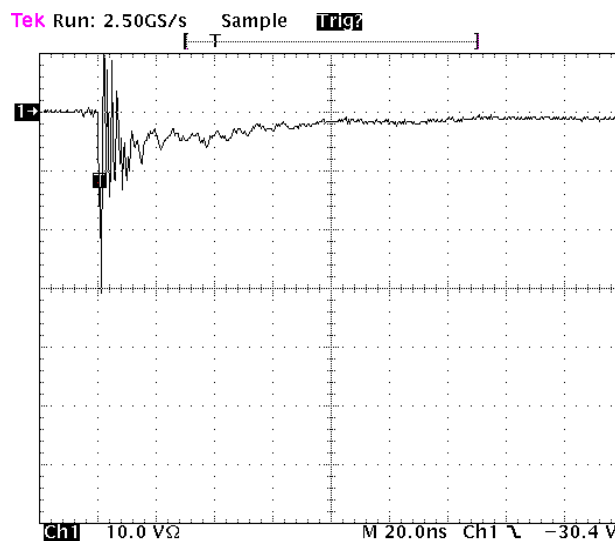


Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2

IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

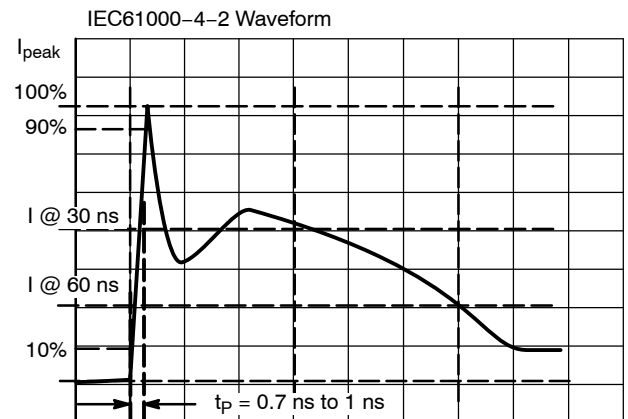


Figure 3. IEC61000-4-2 Spec

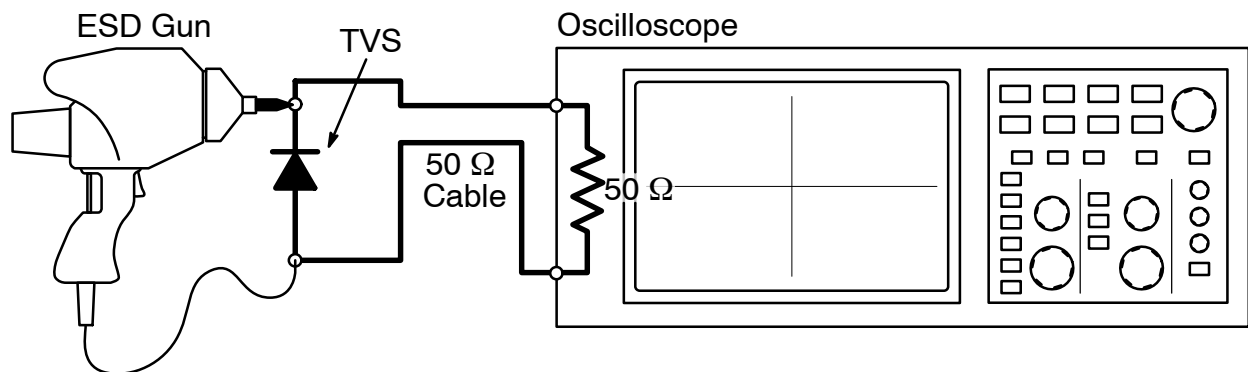


Figure 4. Diagram of ESD Test Setup

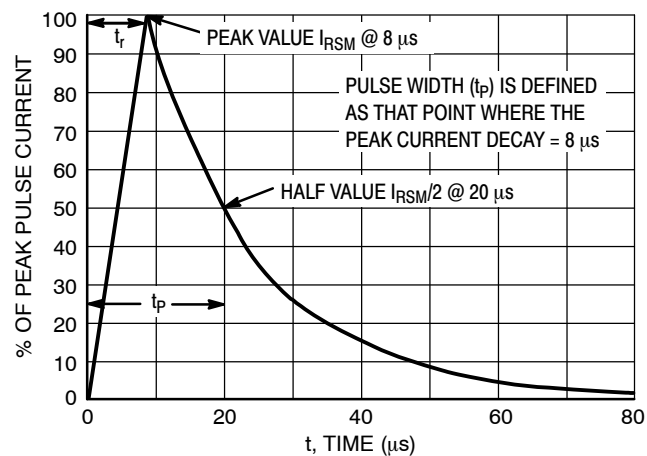
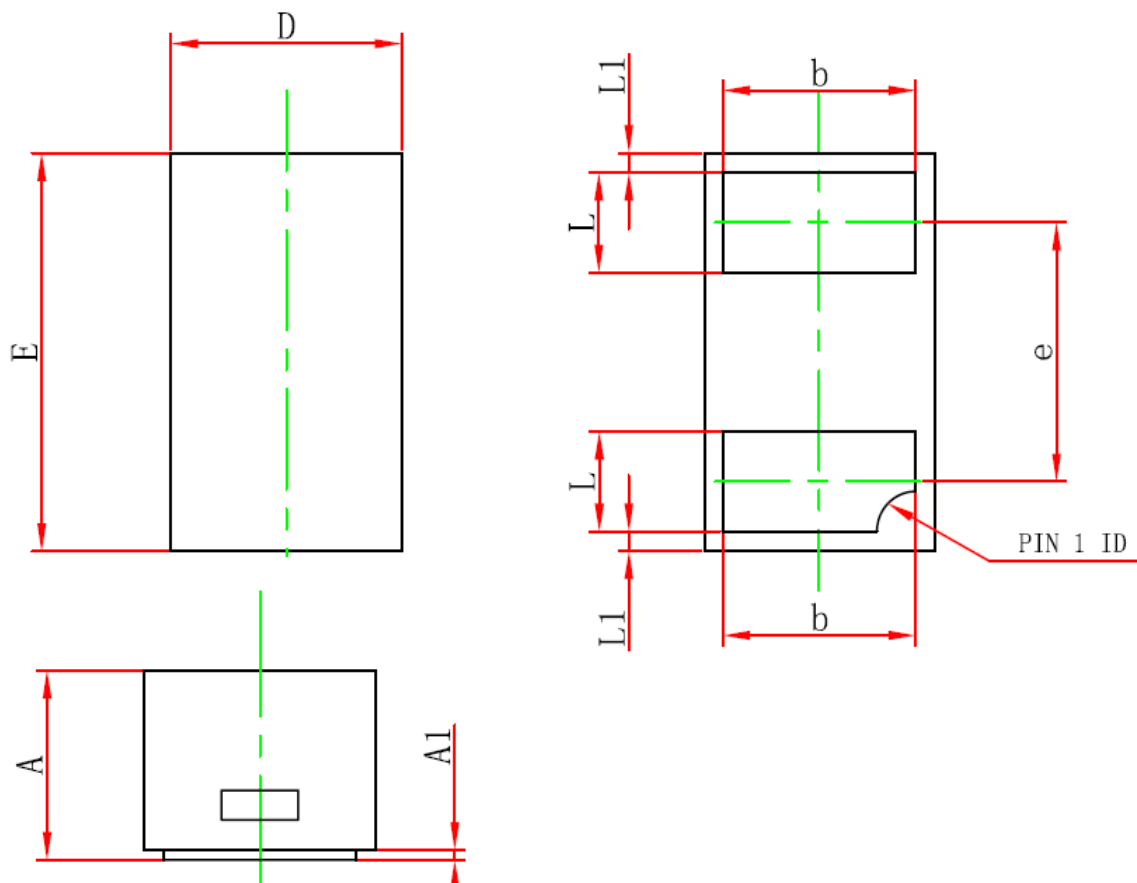


Figure 5. 8 X 20 μ s Pulse Waveform

SOD882 Package Outline Drawing



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.400	0.500	0.016	0.020
A1	0.000	0.050	0.000	0.002
D	0.550	0.650	0.022	0.026
E	0.950	1.050	0.037	0.041
b	0.400	0.600	0.016	0.024
e	0.650TYP.		0.026TYP.	
L	0.150	0.350	0.006	0.014
L1	0.050REF.		0.002REF.	